

ABSTRACT

There is provided a gap fill material forming composition for lithography that is used in dual damascene process and is excellent in flattening property and fill property. Concretely, it is a gap fill material forming composition characterized in that the composition is used in manufacture of semiconductor device by a method comprising coating a photoresist on a semiconductor substrate having a hole with aspect ratio shown in height/diameter of 1 or more, and transferring an image to the semiconductor substrate by use of lithography process, and that comprises a polymer, a crosslinking agent and a solvent.